



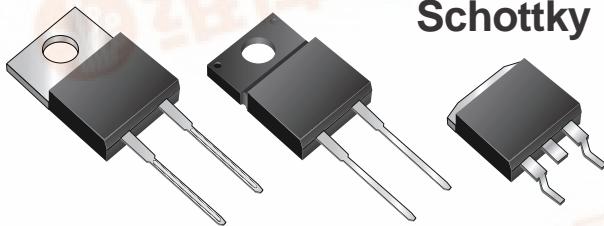
查询MBRB16H35供应商

捷多邦，专业PCB打样工厂，24小时加急出货

MBR16Hxx, MBRF16Hxx & MBRB16Hxx Series

New Product

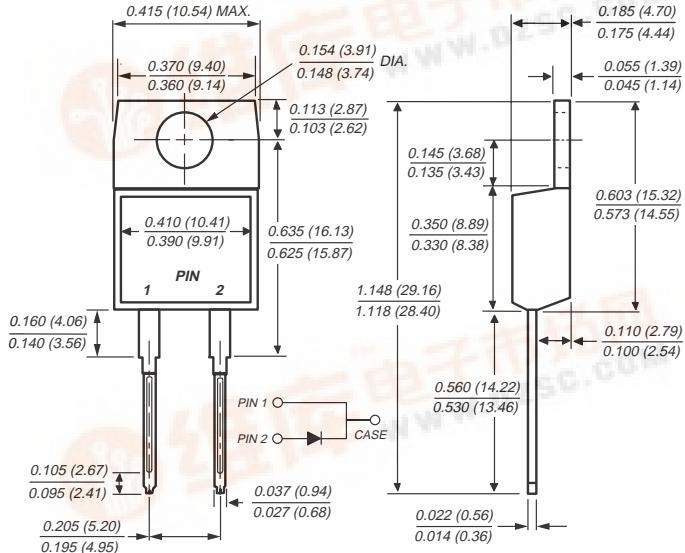
Vishay Semiconductors
formerly General Semiconductor



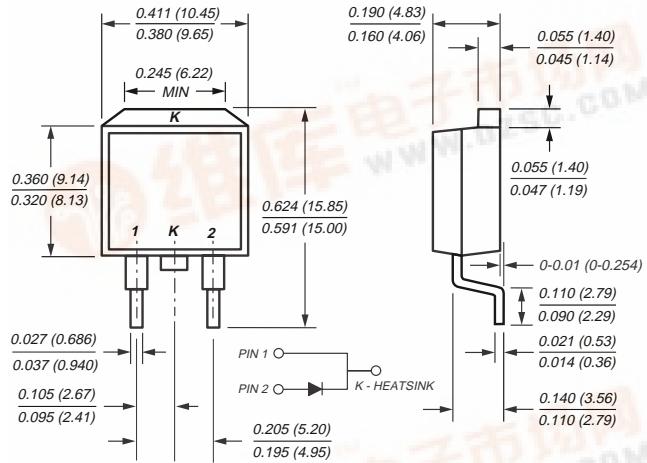
Schottky Barrier Rectifiers

Reverse Voltage 35 to 60 V
Forward Current 16 A

TO-220AC (MBR16Hxx)



TO-263AB (MBRB16Hxx)



Mechanical Data

Case: JEDEC TO-220AC, ITO-220AC & TO-263AB molded plastic body

Terminals: Plated leads, solderable per MIL-STD-750, Method 2026

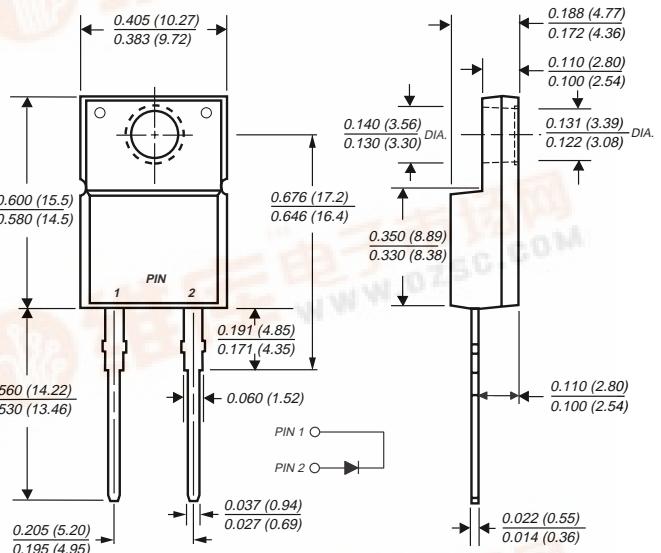
Polarity: As marked

Mounting Position: Any

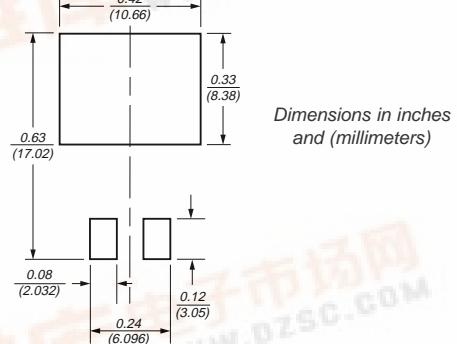
Mounting Torque: 10 in-lbs maximum

Weight: 0.08 oz., 2.24 g

ITO-220AC (MBRF16Hxx)



Mounting Pad Layout TO-263AB



Dimensions in inches
and (millimeters)

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94 V-0
- Metal silicon junction, majority carrier conduction
- Low forward voltage drop, low power loss and high efficiency
- Guardring for overvoltage protection
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- High temperature soldering guaranteed:
250 °C/10 seconds, 0.25" (6.35 mm) from case
- Rated for reverse surge and ESD
- 175 °C maximum operation junction temperature

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Maximum Ratings (T_C = 25 °C unless otherwise noted)

Parameter	Symbol	MBR16H35	MBR16H45	MBR16H50	MBR16H60	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	35	45	50	60	V
Working peak reverse voltage	V _{RWM}	35	45	50	60	V
Maximum DC blocking voltage	V _{DC}	35	45	50	60	V
Max. average forward rectified current (see fig. 1)	I _{F(AV)}		16			A
Peak repetitive forward current at T _C = 150 °C (rated V _R , 20 KHz sq. wave)	I _{FRM}		32			A
Non-repetitive avalanche energy at 25 °C, I _{AS} = 4 A, L = 10 mH	E _{AS}		80			mJ
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}		150			A
Peak repetitive reverse surge current at t _p = 2.0 µs, 1 KHz	I _{RRM}	1.0		0.5		A
Peak non-repetitive reverse energy (8/20 µs waveform)	E _{RSR}		20			mJ
Electrostatic discharge capacitor voltage Human body model: C = 100 pF, R = 1.5 kΩ	V _C		25			kV
Voltage rate of change (rated V _R)	dV/dt		10,000			V/µs
Operating junction temperature range	T _J		−65 to +175			°C
Storage temperature range	T _{STG}		−65 to +175			°C
RMS Isolation voltage (MBRF type only) from terminals to heatsink with t = 1.0 second, RH ≤ 30%	V _{ISOL}	4500 ⁽¹⁾ 3500 ⁽²⁾ 1500 ⁽³⁾				V

Electrical Characteristics (T_C = 25 °C unless otherwise noted)

Parameter	Symbol	MBR16H35, MBR16H45		MBR16H50, MBR16H60		Unit
		Typ	Max	Typ	Max	
Maximum instantaneous forward voltage ⁽⁴⁾ at I _F = 16 A at I _F = 16 A	V _F	— 0.52	0.66 0.56	— 0.58	0.73 0.62	V
Maximum instantaneous reverse current at rated DC blocking voltage ⁽⁴⁾	I _R	— 6.0	100 20	— 4.0	100 20	µA mA

Thermal Characteristics (T_C = 25°C unless otherwise noted)

Parameter	Symbol	MBR	MBRF	MBRB	Unit
Typical thermal resistance from junction to case	R _{θJC}	1.5	3.0	1.5	°C/W

Notes:

- (1) Clip mounting (on case), where lead does not overlap heatsink with 0.110" offset
 (2) Clip mounting (on case), where leads do overlap heatsink
 (3) Screw mounting with 4-40 screw, where washer diameter is ≤ 4.9 mm (0.19")
 (4) Pulse test: 300 µs pulse width, 1% duty cycle

Ordering Information

Product	Case	Package Code	Package Option
MBR16H35 – MBR16H60	TO-220AC	45	Anti-Static tube, 50/tube, 2K/carton
MBRF16H35 – MBRF16H60	ITO-220AC	45	Anti-Static tube, 50/tube, 2K/carton
MBRB16H35 – MBRB16H60	TO-263AB	31 45 81	13" reel, 800/reel, 4.8K/carton Anti-Static tube, 50/tube, 2K/carton Anti-Static 13" reel, 800/reel, 4.8K/carton



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Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Forward Current Derating Curve

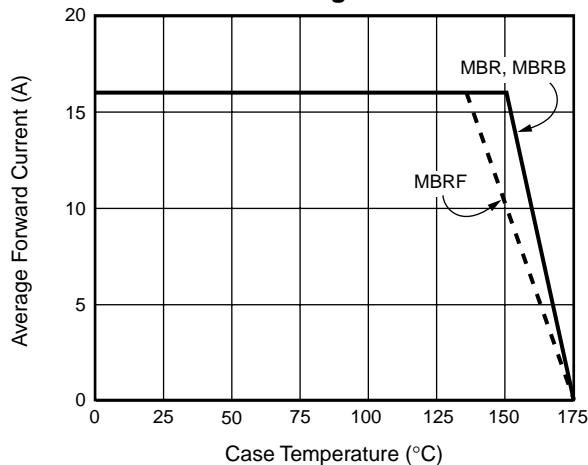


Fig. 2 – Maximum Non-Repetitive Peak Forward Surge Current

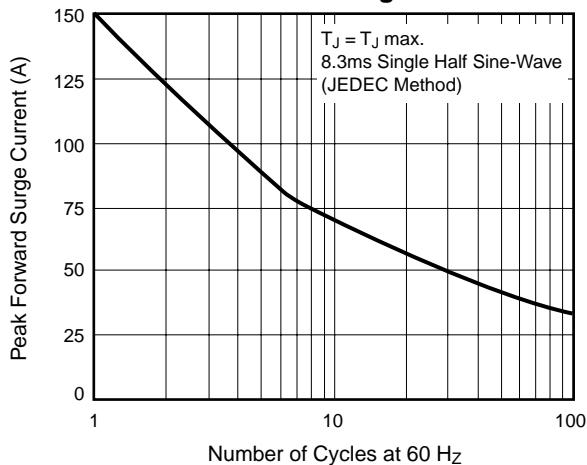


Fig. 3 – Typical Instantaneous Forward Characteristics

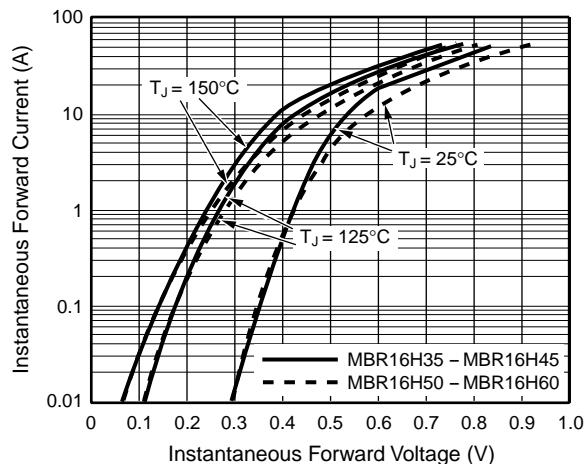


Fig. 4 – Typical Reverse Characteristics

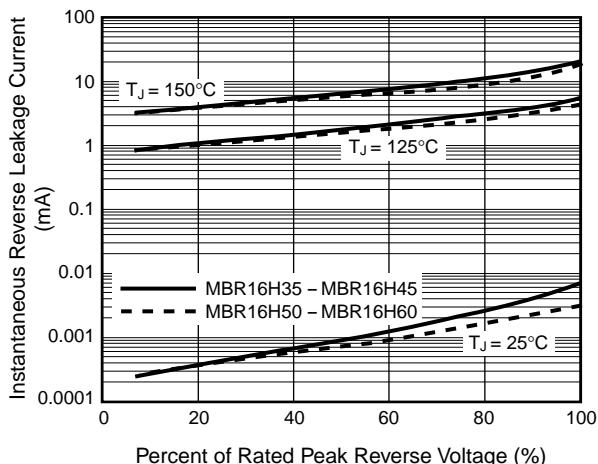


Fig. 5 – Typical Junction Capacitance

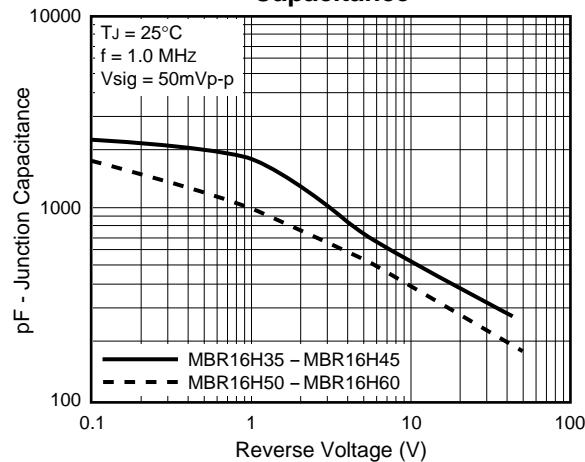


Fig. 6 – Typical Transient Thermal Impedance

